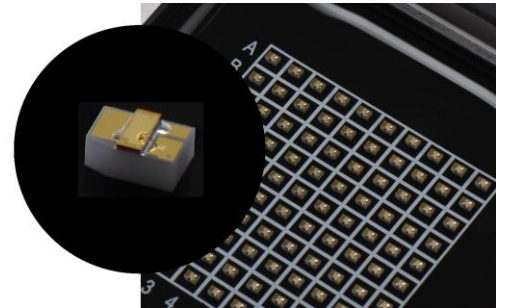


1.5 μ m Gain Chip (chip on sub-mount) **AE5T310BY60P**

AE5T310BY60P is 1.5 μ m InGaAsP / InP Gain Chip for External Cavity Laser developed as a light source for optical fiber communication or optical sensing.

◆ FEATURES

- Broad band: > 100 nm tuning range (CL-band)
- High Optical Output Power: >40 mW with external cavity
- Low spectral ripple
- Normal facet reflectance: LR (6%)



◆ OPTICAL AND ELECTRICAL CHARACTERISTICS (T_{LD}=25°C)

Item	Symbol	Test condition	Min.	Typ.	Max	Unit
Forward Voltage	V _F	IF =200 mA, pulsed (tw=50 μ s)	-	1.4	2.0	V
ASE Output Power	P _{ASE}	IF =200 mA, pulsed (tw=50 μ s)	1	5	-	mW
Center Wavelength	λ_c	IF =100 mA, pulsed (tw=50 μ s)	1530	-	1590	nm
ASE Ripple	M	IF =100 mA, CW at λ_c =1560 nm	-	-	2.0	dB
Beam Exit Angle	$\Delta\theta_R$	IF =200 mA CW	19	20	21	deg.
Beam Divergence Angle Transverse (perpendicular), Normal Facet	θ_t^{NOR}	IF =200 mA CW, FAHM	15	20	25	deg.
Beam Divergence Angle Lateral (parallel), Normal Facet	θ_p^{NOR}	IF =200 mA CW, FAHM	17	20	23	deg.
Beam Divergence Angle Transverse (perpendicular), Angled Facet	θ_t^{ANG}	IF =200 mA CW, FAHM	26	29	32	deg.
Beam Divergence Angle Lateral (parallel), Angled Facet	θ_p^{ANG}	IF =200 mA CW, FAHM	15	18	21	deg.

*We recommend using Gain Chip in an airtight seal for long-term reliability.

◆ **ABSOLUTE MAXIMUM RATINGS** ($T_{LD}=25^{\circ}C$)

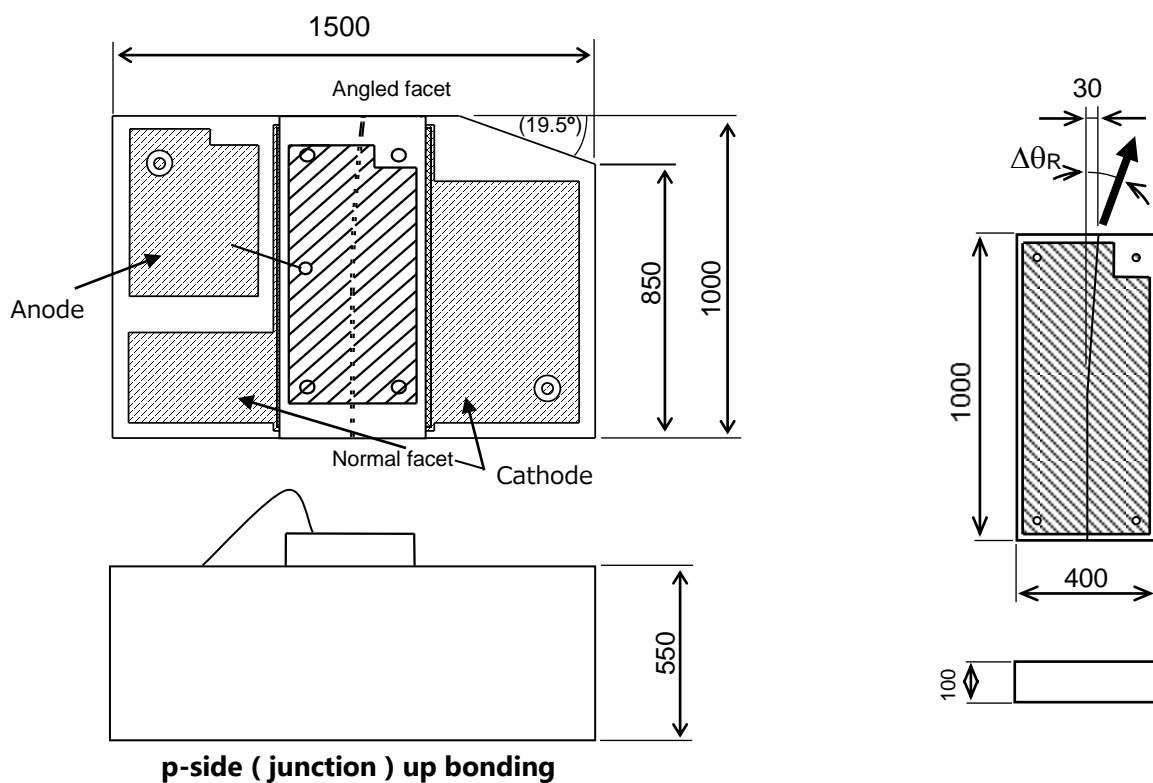
Item	Symbol	Rating	Unit
LD Forward Current	I_F	500	mA
LD Reverse Voltage	V_R	2	V
Operating Case Temperature*	T_C	+15~+45	$^{\circ}C$
Storage Temperature	T_{stg}	-40~+85	$^{\circ}C$
Process/Soldering Temp. vs Time			
Maximum duration 20s	-	300	$^{\circ}C$
Maximum duration 2hour	-	200	$^{\circ}C$
Maximum duration 100hour	-	120	$^{\circ}C$
ESD(Human Body Model)	ESD	500	V

*No condensation

◆ **TECHNICAL SPECIFICATIONS**

Item	Symbol	Test condition	Min.	Typ.	Max.	Unit
Angled facet Reflectance	R^{ANG}	CL-band	-	5×10^{-5}	10^{-4}	-
Normal facet Reflectance	R^{NOR}	CL-band	5	6	7	%
Chip Length	-		0.98	1.00	1.02	mm
Chip Width	-		0.38	0.40	0.42	mm
Chip Height	-		0.09	0.10	0.11	mm

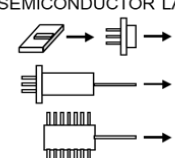
◆ **DIMENSIONS** (Unit : μm)







CAUTION : Handle the fiber of the enclosed device(s) with extreme care ; glass fiber is subject to breakage if mishandled and permanent damage to the device may result. Do not pull the device by the fiber or protective sleeve.
Do not coil the fiber into a loop of than 30 mm in radius.

SEMICONDUCTOR LASER





INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE TO
DIRECT OR SCATTERED RADIATION

 OUTPUT POWER 500mW
WAVELENGTH 0.80 to 1.80 μm
CLASS IIIb LASER PRODUCT

AVOID EXPOSURE
Invisible laser radiation is emitted from this aperture

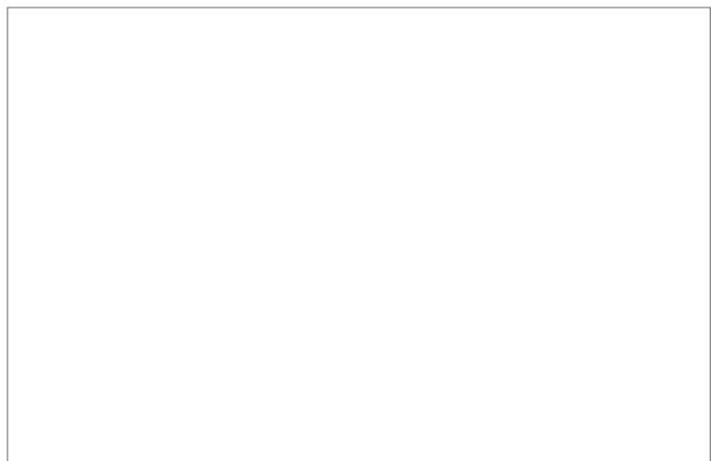
Caution - use of controls or adjustments or performance of procedures other than those specified herein may result in hazardous radiation exposure.
This Product Complies with 21 CFR 1040.10 and 1040.11
Manufactured Anritsu Corp. 5-1-1 Onna, Atsugi-shi, Kanagawa, Japan

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